

**SANYO**

No.2407

**DSC30T**Diffused Junction Type Silicon Diode  
3.0A POWER RECTIFIER**Features**

- Peak reverse voltage  $V_{RM} = -100$  to  $-1000V$
- Average rectified current  $I_o = 3.0A$

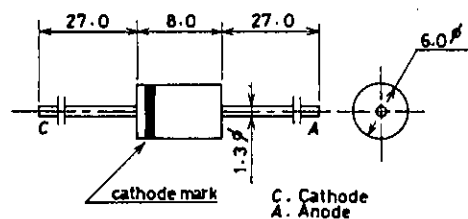
**Absolute Maximum Ratings at  $T_a = 25^\circ C$** 

|                           |                                   | DSC30TB | DSC30TC     | DSC30TE | unit       |
|---------------------------|-----------------------------------|---------|-------------|---------|------------|
| Peak Reverse Voltage      | $V_{RM}$                          | -100    | -200        | -400    | V          |
| Average Rectified Current | $I_o$ $T_a = 50^\circ C$          | →       | →           | 3.0     | A          |
| Surge Forward Current     | $I_{FSM}$ 50Hz sine wave, 1 cycle | →       | →           | 180     | A          |
| Junction Temperature      | $T_J$                             | →       | →           | 150     | $^\circ C$ |
| Storage Temperature       | $T_{stg}$                         |         | -40 to +150 |         | $^\circ C$ |

|                           |                                   | DSC30TG | DSC30TJ     | DSC30TL | unit       |
|---------------------------|-----------------------------------|---------|-------------|---------|------------|
| Peak Reverse Voltage      | $V_{RM}$                          | -600    | -800        | -1000   | V          |
| Average Rectified Current | $I_o$ $T_a = 50^\circ C$          | →       | →           | 3.0     | A          |
| Surge Forward Current     | $I_{FSM}$ 50Hz sine wave, 1 cycle | →       | →           | 130     | A          |
| Junction Temperature      | $T_J$                             | →       | →           | 150     | $^\circ C$ |
| Storage Temperature       | $T_{stg}$                         | →       | -40 to +150 |         | $^\circ C$ |

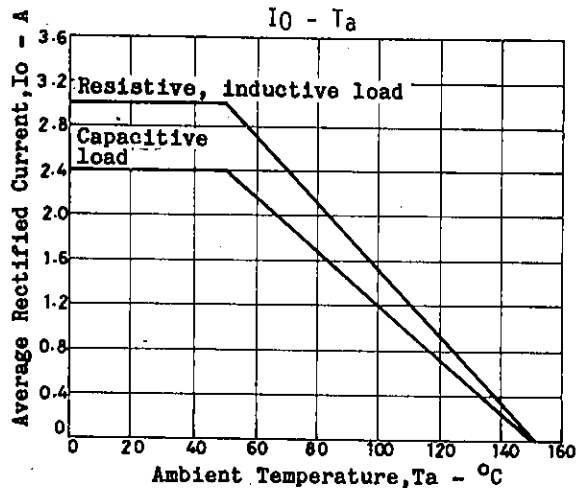
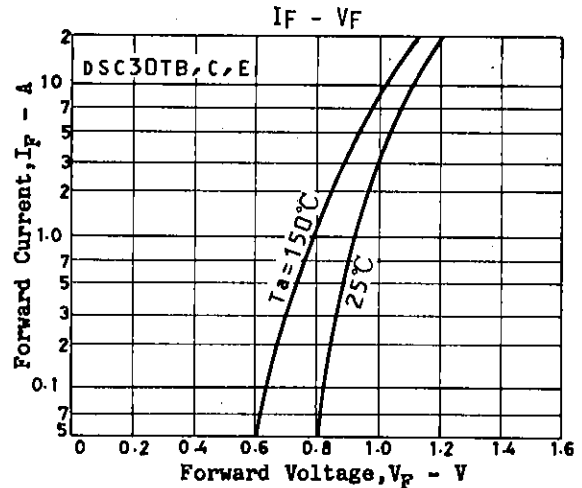
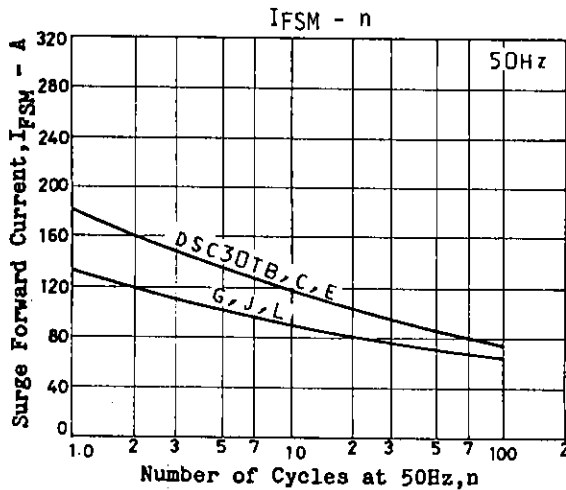
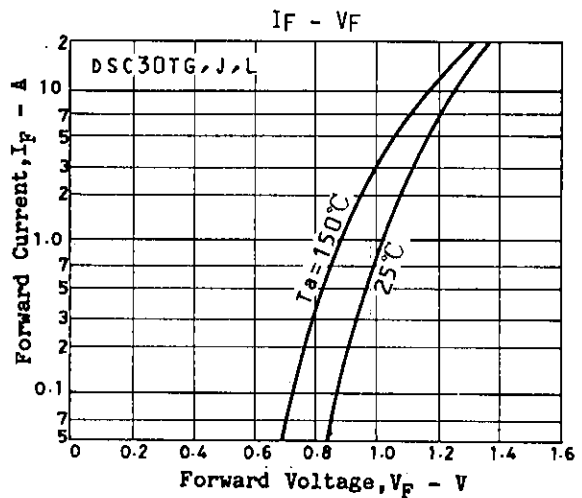
**Electrical Characteristics at  $T_a = 25^\circ C$** 

|                 |                                |  | min | typ | max | unit    |
|-----------------|--------------------------------|--|-----|-----|-----|---------|
| Forward Voltage | $V_F$ $I_F = 3.0A(B, C, E)$    |  |     |     | 1.0 | V       |
|                 | $I_F = 3.0A(G, J, L)$          |  |     |     | 1.1 | V       |
| Reverse Current | $I_R$ $V_R$ : At each $V_{RM}$ |  |     |     | -10 | $\mu A$ |

**Package Dimensions 1176**  
(unit: mm)**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

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